

Silicon Controlled Rectifiers

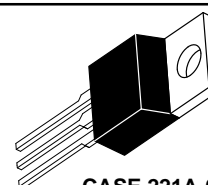
Reverse Blocking Triode Thyristors

... designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half-wave silicon gate-controlled, solid-state devices are needed.

- Glass Passivated Junctions with Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts

**S2800
Series**

**SCRs
10 AMPERES RMS
50 thru 800 VOLTS**



**CASE 221A-04
(TO-220AB)
STYLE 3**

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage ⁽¹⁾ (T _J = 25 to 100°C, Gate Open)	V _{RRM} V _{DRM}		Volts
F		50	
A		100	
B		200	
S2800 D		400	
M		600	
N		800	
Peak Non-repetitive Reverse Voltage and Non-Repetitive Off-State Voltage ⁽¹⁾	V _{RSM} V _{DSM}		Volts
F		75	
A		125	
B		250	
S2800 D		500	
M		700	
N		900	
RMS Forward Current (All Conduction Angles)	I _{T(RMS)}	10	Amps
T _C = 75°C			
Peak Forward Surge Current (1 Cycle, Sine Wave, 60 Hz, T _C = 80°C)	I _{TSM}	100	Amps
Circuit Fusing Considerations (t = 8.3 ms)	I ² t	40	A ² s
Forward Peak Gate Power (t ≤ 10 μs)	P _{GM}	16	Watts
Forward Average Gate Power	P _{G(AV)}	0.5	Watt
Operating Junction Temperature Range	T _J	-40 to +100	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

S2800 Series

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current ($V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}, \text{ Gate Open}$) $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$	I_{DRM}, I_{RRM}	— —	— —	10 2	μA mA
Instantaneous On-State Voltage, ($I_{TM} = 30 \text{ A Peak, Pulse Width } \leq 1 \text{ ms, Duty Cycle } \leq 2\%$)	V_T	—	1.7	2	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ Vdc, } R_L = 30 \text{ Ohms}$)	I_{GT}	—	8	15	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc, } R_L = 30 \text{ Ohms}$)	V_{GT}	—	0.9	1.5	Volts
Holding Current (Gate Open, $V_D = 12 \text{ Vdc, } I_T = 150 \text{ mA}$)	I_H	—	10	20	mA
Gate Controlled Turn-On Time ($V_D = \text{Rated } V_{DRM}, I_{TM} = 2 \text{ A, } I_{GR} = 80 \text{ mA}$)	t_{gt}	—	1.6	—	μs
Circuit Commutated Turn-Off Time ($V_D = V_{DRM}, I_{TM} = 2 \text{ A, Pulse Width} = 50 \mu s,$ $dv/dt = 200 \text{ V}/\mu s, di/dt = 10 \text{ A}/\mu s, T_C = 75^{\circ}C$)	t_q	—	25	—	μs
Critical Rate-of-Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}, \text{ Exponential Rise, } T_C = 100^{\circ}C$)	dv/dt	—	100	—	$V/\mu s$

FIGURE 1 – CURRENT DERATING

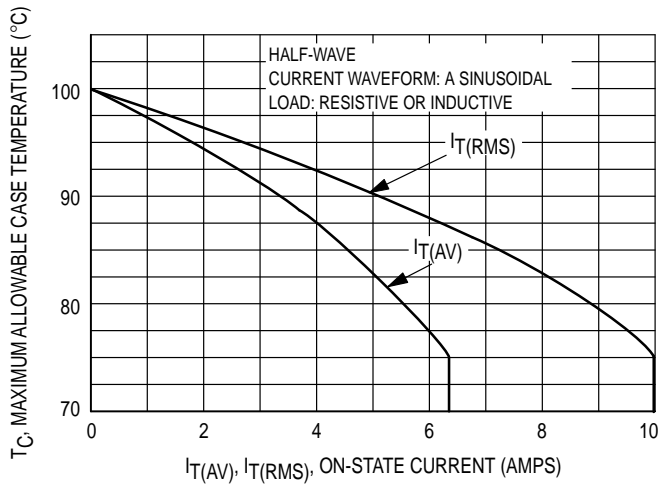
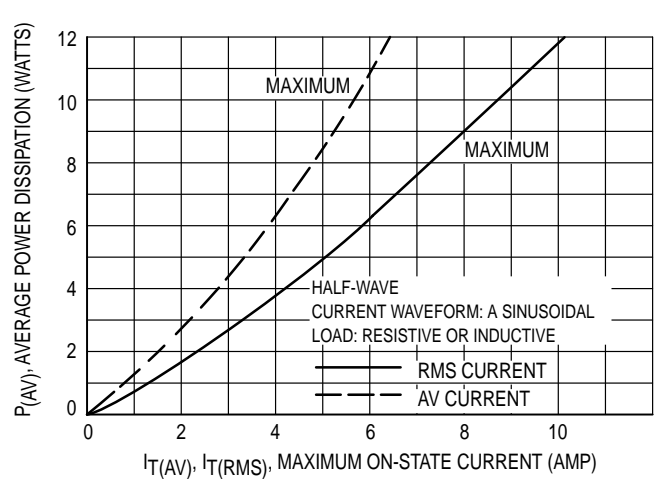
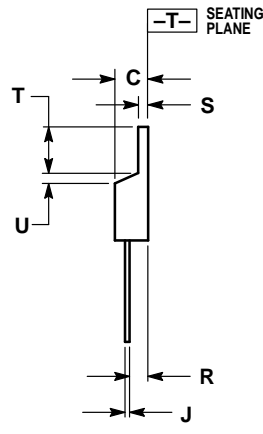
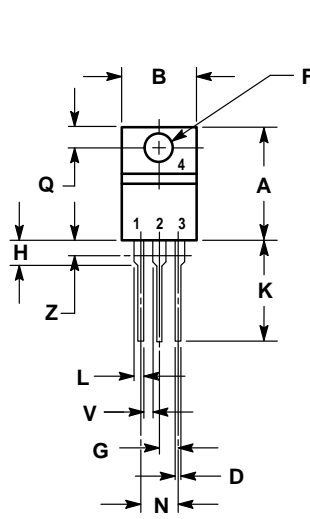


FIGURE 2 – POWER DISSIPATION



PACKAGE DIMENSIONS



STYLE 3:
 PIN 1. CATHODE
 2. ANODE
 3. GATE
 4. ANODE

NOTES:
 1. DIMENSION AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.055	1.15	1.39
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

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 (TO-220AB)

S2800 Series

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S2800/D

